PNA2603L

Darlington Phototransistor

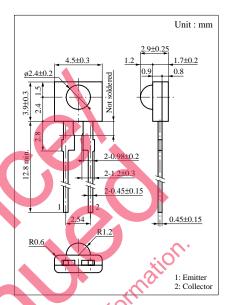
For optical control systems

Features

- Darlington output, high sensitivity
- Easy to combine light emission and photodetection on same printed circuit board
- Small size, thin side-view type package



Parameter	Symbol	Ratings	Unit	
Collector to emitter voltage	V _{CEO}	20	V	
Emitter to collector voltage	V _{ECO}	5	V	
Collector current	I _C	30	mA	
Collector power dissipation	P _C	100	mW	
Operating ambient temperature	T_{opr}	-25 to +80	°C	
Storage temperature	T _{stg}	-30 to +100	°C	

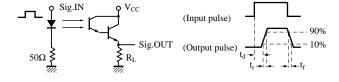


Electro-Optical Characteristics (Ta = 25°C)

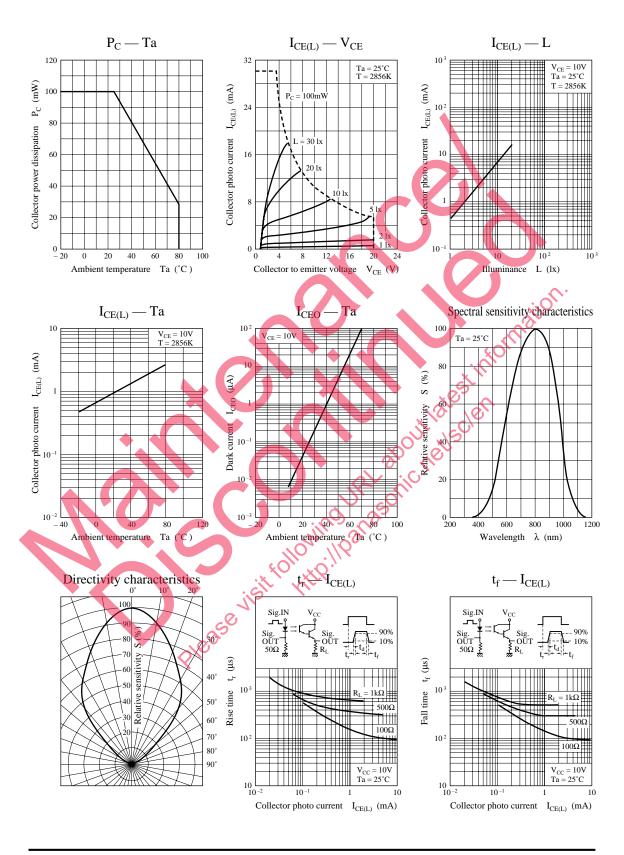
Collector to emitter voltage	V _{CEO}	20	V			dille	1: Emitter
Emitter to collector voltage	V _{ECO}	5	V		e ^r	40	2: Collector
Collector current	I_{C}	30	mA		(0)	,	
Collector power dissipation	P _C	100	mW		A.		
Operating ambient temperature	Topr	-25 to +80	°C	01			
Storage temperature	T _{stg}	-30 to +100	°C	Silve	18/		
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■ Electro-Optical Charac	cteristics	s (Ta = 25°C)	JRLSO	nic. Petis			
■ Electro-Optical Charac	cteristics		nditions	min min	typ	max	Unit
			250	,			Unit μΑ
Parameter	Symbol	Cor	nditions	,	typ	max	_
Parameter Dark current	Symbol I _{CEO}	V _{CE} = 10V	nditions	min	typ 0.1	max	μΑ
Parameter Dark current Collector photo current	$\begin{array}{c} \text{Symbol} \\ I_{\text{CEO}} \\ I_{\text{CE(L)}} \end{array}$	$\begin{aligned} & & & & & & & & & & & & & & \\ & & & & $	nditions	0.2	typ 0.1	max	μA mA
Parameter Dark current Collector photo current Peak sensitivity wavelength	$\begin{array}{c} \text{Symbol} \\ I_{CEO} \\ I_{CE(L)} \\ \lambda_{P} \end{array}$	$\begin{aligned} & & & & & & & & & & & & & & \\ & & & & $	nditions 2.1 x^{+1} cal axis to the half power $x^{-1} = 5mA, R_L = 1$	min 0.2 er point	typ 0.1 1 800	max	μA mA nm

^{*1} Measurements were made using a lungsten lamp (color temperature T = 2856K) as a light source.

^{*2} Switching time measurement circuit



- t_d: Delay time
- t_r: Rise time (Time required for the collector photo current to increase from 10% to 90% of its final value)
- t_f: Fall time (Time required for the collector photo current to decrease from 90% to 10% of its initial value)



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